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**PATENT**  
Attorney Docket No.: 000939-073311US  
Client Ref. No.: P01HA010/US

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

On July 25, 2003

TOWNSEND and TOWNSEND and CREW LLP

By: [Signature]

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of:

Hong Koo Kim

Application No.: 09/747,779

Filed: December 22, 2000

For: FABRICATION METHOD AND  
STRUCTURE FOR FERROELECTRIC  
NONVOLATILE MEMORY FIELD  
EFFECT TRANSISTOR

Examiner: Marcos D. Pizarro Crespo

Technology Center/Art Unit: 2814

PRELIMINARY AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Prior to examination of the above-referenced application, please enter the following amendments and remarks:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 6 of this paper.

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01 FC:1202 126.00 DA  
02 FC:1201 84.00 DA